

TQTRp Process Cross-Section

Features

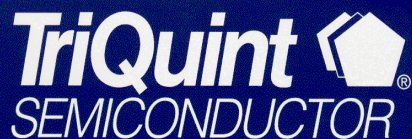
- High Density Interconnects:
 - 3 Global
 - 1 Local
 - 9 μm Total Thickness
- High-Q Passives; >50 @ 2 GHz
- 0.6 μm Gate Length MESFET Optional: Power & General Purpose D-FETs; E-FET
- Schottky-Barrier Diodes
- Bulk & Thin Film Resistors
- High Value Capacitors
- Dielectric Encapsulated Metals
- Planarized Surface; simplified plastic packaging
- Substrate Vias Available
- Volume Production Processes
- Low Cost Passives-Only Option

Applications

- Active and/or Passive Components
- Circuits Requiring High Q Passive Elements
- Ideal for Mixers, Converters, and Phase-Shifters with Baluns, Transformers, E-M Structures
- Mobile Phone Front End Blocks
- RF Module Front-Ends

General Description

TriQuint's TQTRp process has advanced metal systems and MESFET devices. It is targeted at high performance, small size passive-only or passive/active circuits and utilizes over 9 μm of gold metal. High density interconnections are accomplished with three thick global and one surface metal interconnect layers. The four metal layers are encapsulated in a high performance dielectric that allows wiring flexibility and plastic packaging simplicity. Precision NiCr resistors, implanted resistors, and high value MIM capacitors are included. Advanced 0.6 μm enhancement/depletion mode MESFET devices include an integrated power MESFET, general purpose D-Mode MESFET, and Enhancement Mode MESFET and are based on the TQTRx process, currently TriQuint's highest volume process. The TQTRp process is available on 150-mm (6 inch) wafers.



TQTRp

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**TQTRp
Process
Details**

Element	Parameter	Value	Units
Interconnects	Metal Layers	Four: 0.5,2,2,5	um
MIM Caps	Values	1200	pF/mm2
Resistors	NiCr	50	Ohms/sq
	Bulk	700	Ohms/sq
Gate Length	(All FETs)	0.6	um
N+ Diode	Vforward	0.55	V
E-FET;	Threshold Voltage	+0.15	V _{th} —V
	I _{max}	90	mA/mm
	F _t @ I _{dss}	18	GHz
	G _m	225	mS/mm
	Breakdown, V _{gd}	22	V
	F _{min} , 6 GHz	0.90	dB
D-FET	Pinchoff Voltage	-0.6	V _p —V
	I _{dss}	70	mA/mm
	G _m	200	mS/mm
	Breakdown, V _{gd}	18.5	V
	F _{min} , 6 GHz	0.54	dB
G-FET	Pinchoff Voltage	-2.2	V _p —V
	I _{dss}	270	mA/mm
	I _{max}	365	mA/mm
	G _m	170	mS/mm
	Breakdown, V _{gd}	19	V
Vias		Yes	
Mask Layers	No Vias	18	
	With Vias	20	

**Maximum
Ratings**

FET Operating Channel Temp		-55 to +150	°C
Capacitor Breakdown Voltage	- Design	10	V
	- Typical	20	V

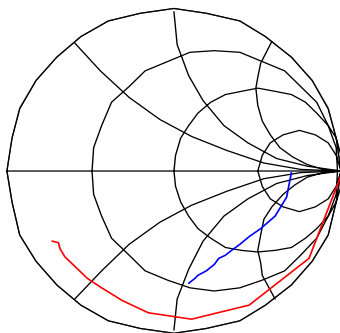
Specifications Subject to Change



TQTRp

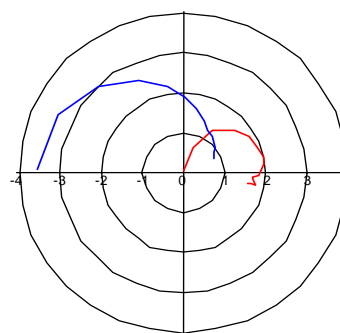
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GFET
 300 um
 Vds=3V
 50% Idss



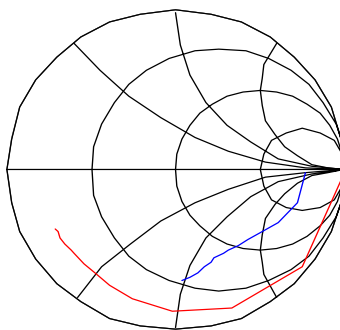
S11
S22

Freq (0.1GHz to 26.1GHz)



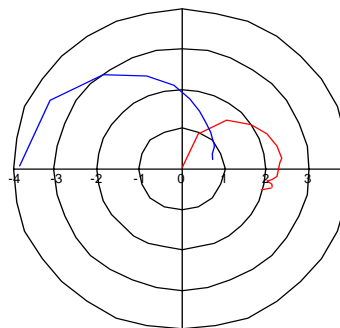
S12 / .05
S21

DFET
 300 um
 Vds=3V
 50% Idss



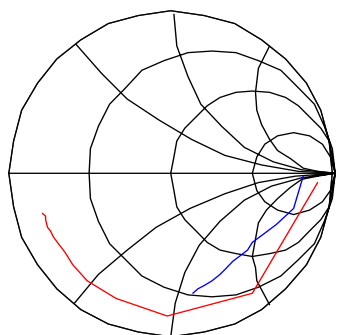
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Freq (0.1GHz to 26.1GHz)



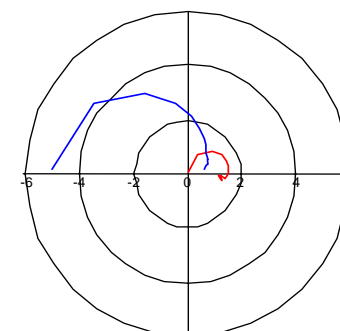
S12 / .05
S21

EFET
 300 um
 Vds=3V
 50% Idmax

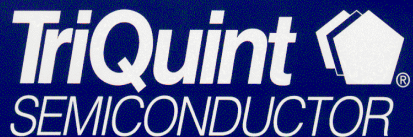


S11
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Freq (0.1GHz to 26.1GHz)



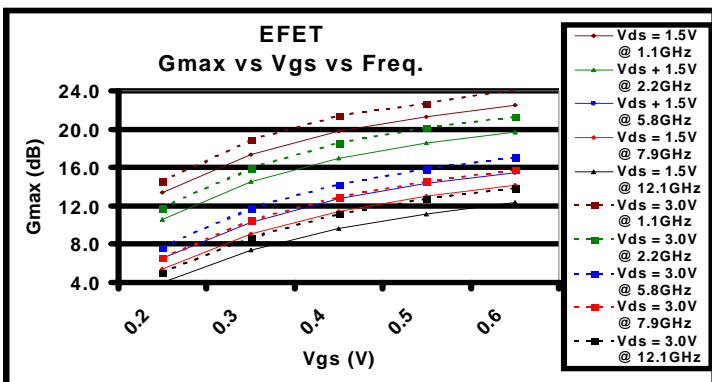
S12 / .05
S21



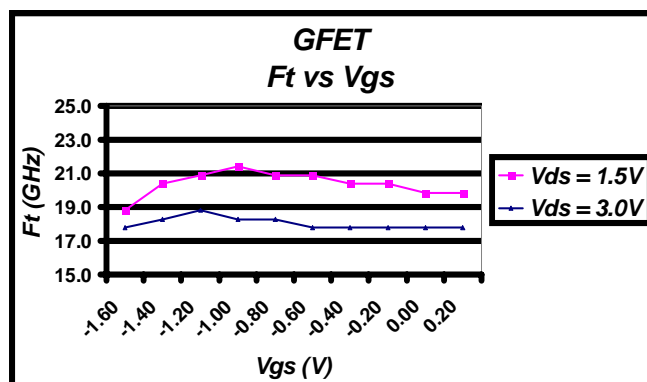
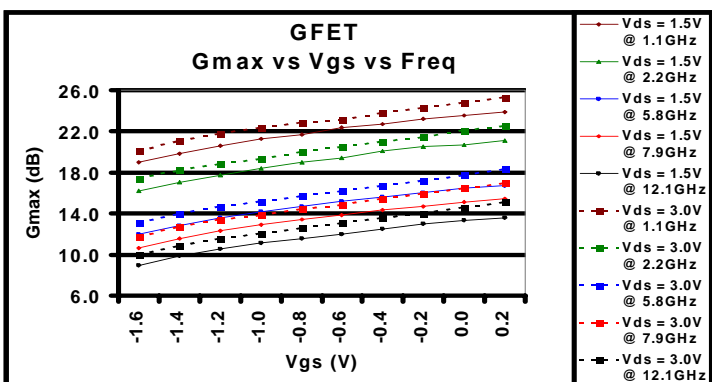
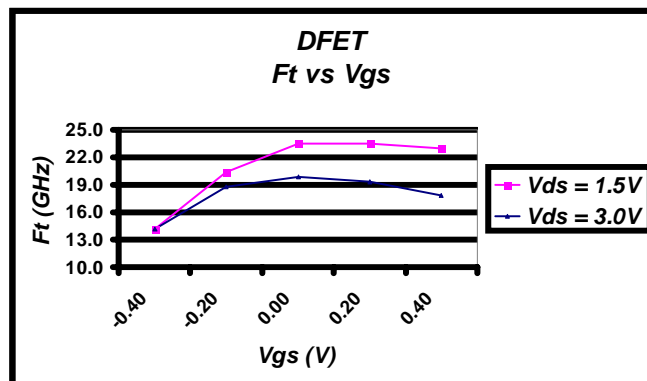
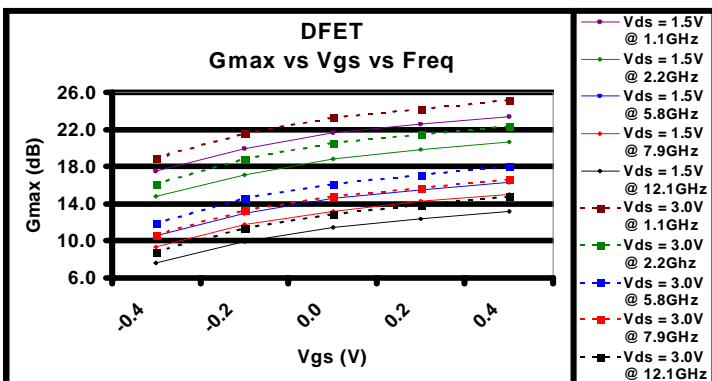
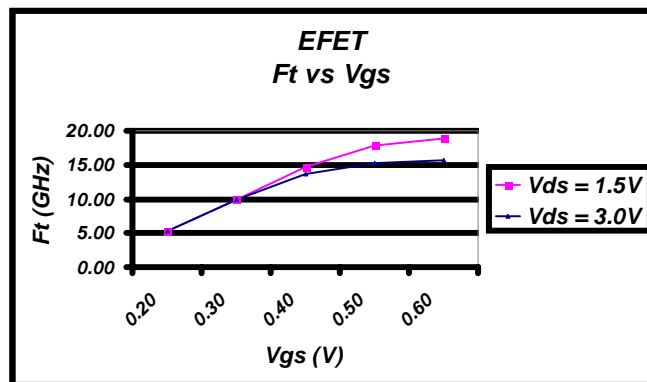
TQTRp

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Gmax vs Vgs vs Frequency
 300 um FETs; Three Types
 Vds = 1.5 & 3.0 V; T=27°C



Ft versus Vgs;
 300 um FETs; Three Types;
 Vds = 1.5 & 3.0 V; T=27°C

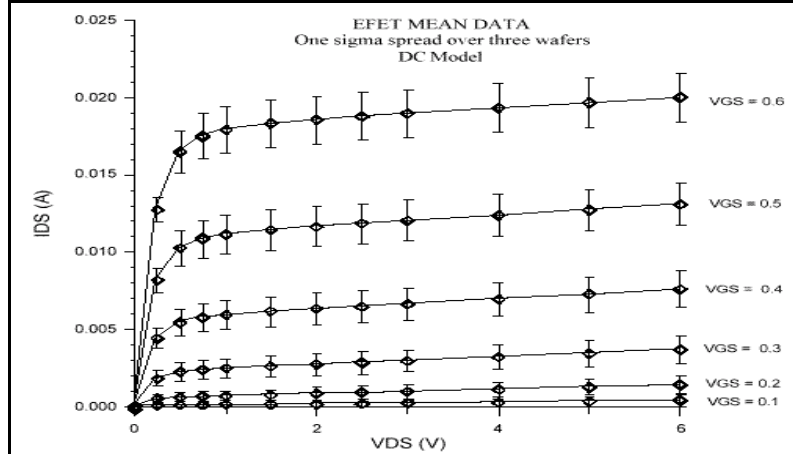




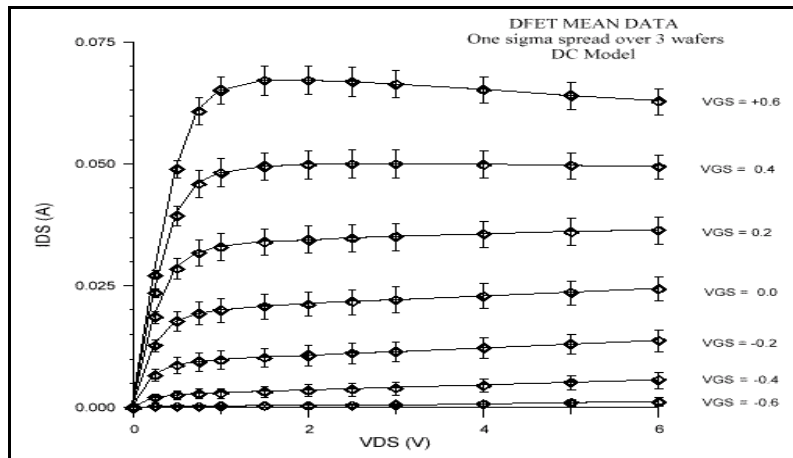
TQTRp

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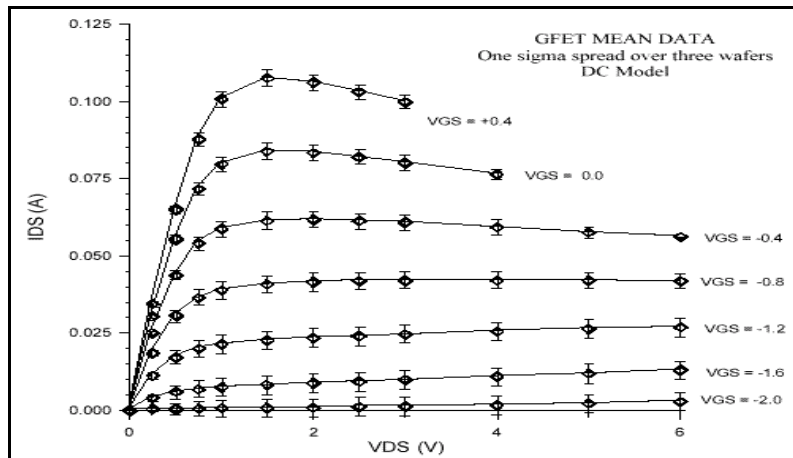
**EFET
IV Curves
300 um**

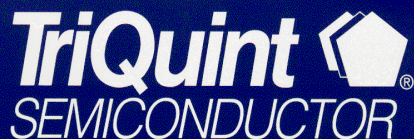


**DFET
IV Curves
300 um**



**GFET
IV Curves
300 um**





TQTRp

Advanced Passives & MESFET Foundry Service

Prototyping and Development

- Prototype Development Quickturn (PDQ):
 - Shared Mask Set;
 - Run Monthly;
 - Hot Lot Cycle;
 - Via and Non-Via Options.
- Prototype Wafer Option (PWO):
 - Customer-specific Masks, Customer Schedule
 - 2 wafers delivered
 - Hot Lot Cycle Time
 - With thinning and sawing; optional backside vias
- Design Sensitivity Test (DST) Wafer Run
 - Yield Analysis
 - Design Sensitivity to Process Variation
 - 14 Wafer Start; Spread of Vp Values

Process Qualification Status

- TQTRp is a fully released qualified process
- Reliability Reports
 - TQTRp Process Qualification
 - TQTRx Element Qualification Report (for FETs)
- For more information on Quality and Reliability, contact TriQuint or visit www.tqs.com/Manufacturing/QR/bdy_qr-pubs.htm.

Design Tool Status

- Design Manual Available Now
- Device Library of Circuit Elements: FETs, Diodes, Thin Film and Implanted Resistors, Capacitors, Inductors
- Parameters for "TriQuint's Own Model" (TOM)
- Agilent ADS Design Kit Available Now
- PSPICE Models Available Q2'02
- Cadence Layout Library Available Now
- Layout/Verification Kit for ICEditors in Q4'02

Applications Support Services

- Tiling of GDSII Stream Files including PCM on 15 x 15 mm maximum Tile Size
- Design Rule Check Services
- Layout versus Schematic Check Services
- Engineering Services:
 - Packaging Development
 - On-Wafer Test Development
 - Packaged Parts
 - Thermal Analysis
 - Yield Enhancement
- Part Qualification Services
- Failure Analysis

Training

- GaAs Design Classes:
 - Half Day Introduction; Upon Request
 - Four Day Technical Training; Fall & Spring at TriQuint Oregon facility
- For Training Schedules please visit: www.triquint.com/foundry

Manufacturing Services

- Mask Making
- Production 150 mm Wafer Fab
- Wafer Thinning
- Wafer Sawing
- Substrate Vias
- DC Die Sort Testing
- RF On-Wafer Testing
- Plastic Packaging
- RF Packaged Part Testing

Please contact your local TriQuint Semiconductor Representative or Foundry Services Staff for additional information:
E-mail: sales@triquint.com Phone: (503) 615-9000 Fax: (503) 615-8905